

MOSFET (N-Channel)

| $V_{(BR)DSS}$ | $R_{DS(on)MAX}$ | I_D |
|---------------|-----------------|-------|
| 60V | 5Ω@10V | 115mA |
| | 7Ω@5V | |

FEATURE

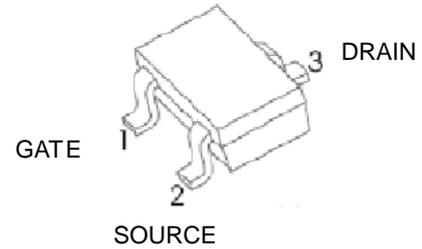
- High density cell design for low $R_{DS(ON)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability

APPLICATION

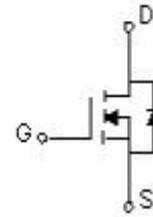
- Load Switch for Portable Devices
- DC/DC Converter

Marking : K72

Package



SOT-523



MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|---|-----------------|-----------|------|
| Drain-Source Voltage | V_{DS} | 60 | V |
| Gate-Source Voltage | V_{GS} | 20 | V |
| Continuous Drain Current | I_D | 0.115 | A |
| Power Dissipation | P_D | 0.200 | W |
| Thermal Resistance from Junction to Ambient | $R_{\theta JA}$ | 625 | °C/W |
| Junction Temperature | T_J | 150 | °C |
| Storage Temperature | T_{stg} | -50 ~+150 | |



MOSFET ELECTRICAL CHARACTERISTICS

Ta=25 °C unless otherwise specified

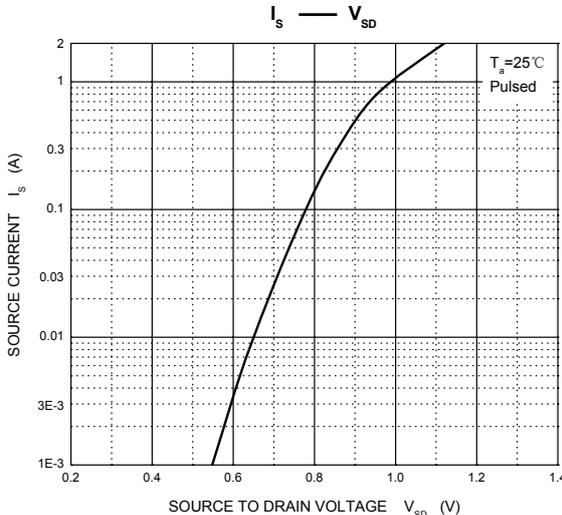
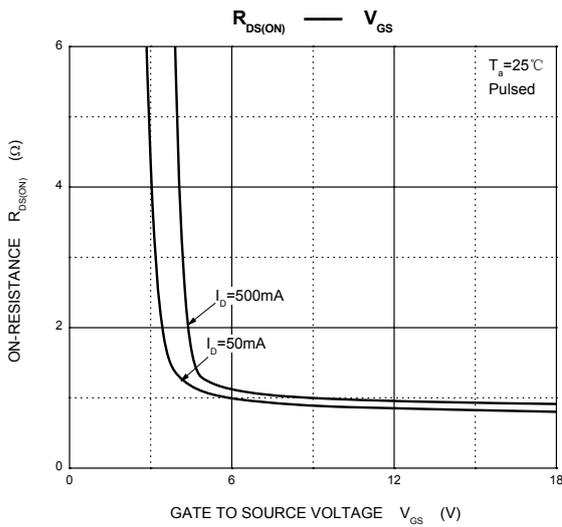
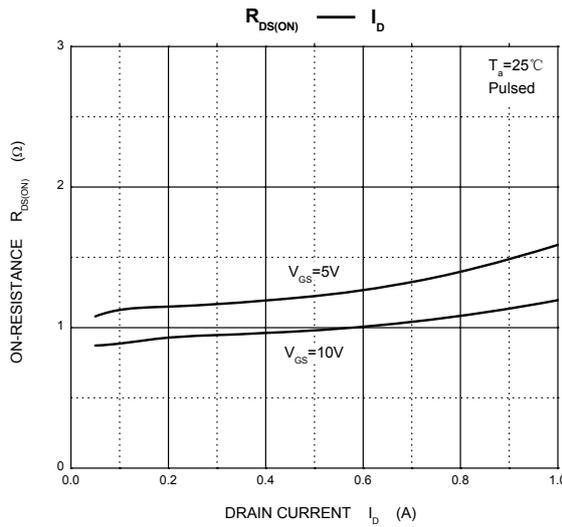
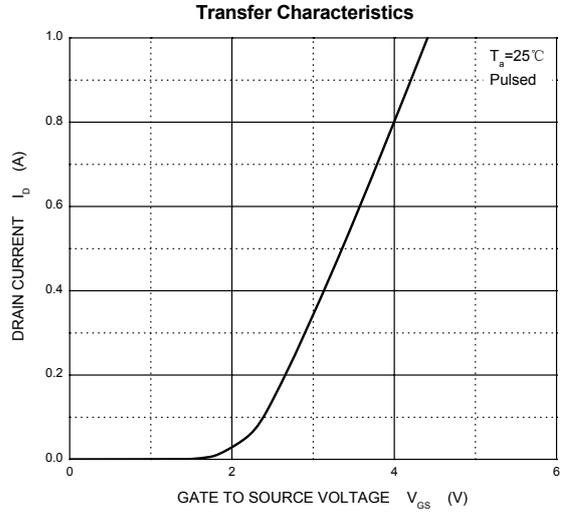
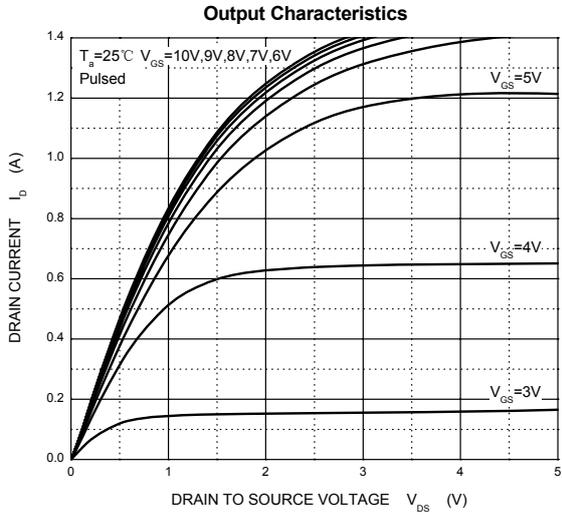
| Parameter | Symbol | Test conditions | Min | Typ | Max | Unit |
|---------------------------------|---------------|---------------------------------|------|-----|----------|----------|
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS}=0V, I_D=250\mu A$ | 60 | | | V |
| Gate-Threshold Voltage | $V_{(GS)th}$ | $V_{DS}=V_{GS}, I_D=250\mu A$ | 1 | 1.6 | 2.5 | |
| Gate-body Leakage | I_{GSS} | $V_{DS}=0V, V_{GS}=\pm 20V$ | | | ± 80 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS}=60V, V_{GS}=0V$ | | | 80 | nA |
| On-state Drain Current | $I_{D(on)}$ | $V_{GS}=10V, V_{DS}=7V$ | 500 | | | mA |
| Drain-Source On-Resistance | $R_{DS(on)}$ | $V_{GS}=10V, I_D=500mA$ | | | 5 | Ω |
| | | $V_{GS}=5V, I_D=50mA$ | | | 7 | |
| Forward Trans conductance | g_{fs} | $V_{DS}=10V, I_D=200mA$ | 80 | | | ms |
| Drain-source on-voltage | $V_{DS(on)}$ | $V_{GS}=10V, I_D=500mA$ | | | 3.75 | V |
| | | $V_{GS}=5V, I_D=50mA$ | | | 0.375 | V |
| Diode Forward Voltage | V_{SD} | $I_S=115mA, V_{GS}=0V$ | 0.55 | | 1.2 | V |
| Input Capacitance * | C_{iss} | $V_{DS}=25V, V_{GS}=0V, f=1MHz$ | | | 50 | pF |
| Output Capacitance * | C_{oss} | | | | 25 | |
| Reverse Transfer Capacitance* | C_{rss} | | | | 5 | |

SWITCHING TIME

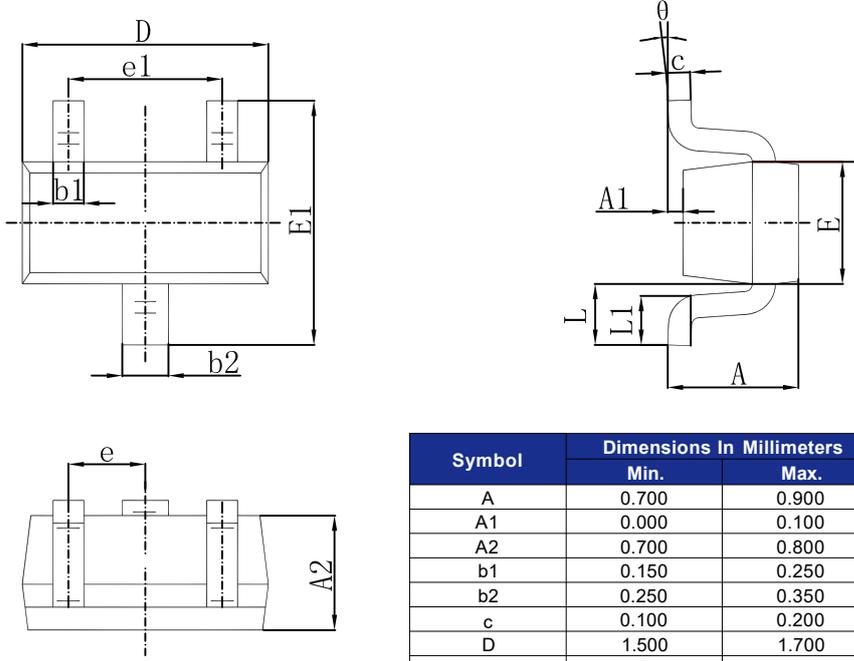
| | | | | | | |
|----------------|--------------|--|----------------|--|----|----|
| Turn-on Time* | $t_{d(on)}$ | $V_{DD}=25V, R_L=50\Omega, I_D=500mA, V_{GEN}=10V$ | | | 20 | ns |
| Turn-off Time* | $t_{d(off)}$ | | $R_G=25\Omega$ | | | |

*These parameters have no way to verify.

Typical Characteristics

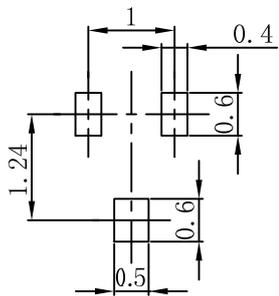


SOT-523 Package Outline Dimensions



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 0.700 | 0.900 | 0.028 | 0.035 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 0.700 | 0.800 | 0.028 | 0.031 |
| b1 | 0.150 | 0.250 | 0.006 | 0.010 |
| b2 | 0.250 | 0.350 | 0.010 | 0.014 |
| c | 0.100 | 0.200 | 0.004 | 0.008 |
| D | 1.500 | 1.700 | 0.059 | 0.067 |
| E | 0.700 | 0.900 | 0.028 | 0.035 |
| E1 | 1.450 | 1.750 | 0.057 | 0.069 |
| e | 0.500 TYP. | | 0.020 TYP. | |
| e1 | 0.900 | 1.100 | 0.035 | 0.043 |
| L | 0.400 REF. | | 0.016 REF. | |
| L1 | 0.260 | 0.460 | 0.010 | 0.018 |
| θ | 0° | 8° | 0° | 8° |

SOT-523 Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: ±0.05mm.
 3. The pad layout is for reference purposes only.